

BSS8402DW

COMPLEMENTARY PAIR ENHANCEMENT MODE MOSFET

Product Summary

Device	BV _{DSS}	RDS(ON) Max	I _D T _A = +25°C
Q1	60V	13.5Ω @ V _{GS} = 10V	115mA
Q2	-50V	10Ω @ V _{GS} = -5V	-130mA

Description

This MOSFET has been designed to minimize the on-state resistance $(R_{DS(ON)})$ and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- General Purpose Interfacing Switch
- Power Management Functions
- Analog Switch

SOT363



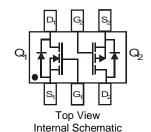
Top View

Features and Benefits

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Complementary Pair
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Mechanical Data

- Case: SOT363
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish Annealed over Alloy 42 Leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208 @3
- Terminal Connections: See Diagram
- Weight: 0.006 grams (Approximate)



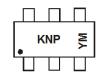
Ordering Information (Note 5)

Part Number	Compliance	Case	Packaging
BSS8402DW-7-F	Standard	SOT363	3,000/Tape & Reel
BSS8402DW-13-F	Standard	SOT363	10,000/Tape & Reel
BSS8402DWQ-7	Automotive	SOT363	3,000/Tape & Reel
BSS8402DWQ-13	Automotive	SOT363	10,000/Tape & Reel

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to https://www.diodes.com/quality/.
- 5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



 $\begin{array}{l} \text{KNP} = \text{Product Type Marking Code} \\ \text{YM or } \overline{\text{Y}} \text{M= Date Code Marking} \\ \text{Y or } \overline{\text{Y}} = \text{Year (ex: F = 2018)} \\ \text{M = Month (ex: 9 = September)} \end{array}$

Date Code Key

Year	2003	2004	2005	2006	~	2018	2019	2020	2021	2022	2023	2024	2025	2026
Code	Р	R	S	Т	~	F	G	Н	I	J	K	L	М	N
Month	Jan	Feb	М	ar	Apr	May	Jun	Jul	Aug	Se	р	Oct	Nov	Dec
Code	1	2	3	3	4	5	6	7	8	9		0	N	D



Maximum Ratings - Total Device (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 6)	P_{D}	200	mW
Thermal Resistance, Junction to Ambient	$R_{ heta JA}$	625	°C/W
Operating and Storage Temperature Range	T _{J,} T _{STG}	-55 to +150	°C

Maximum Ratings N-CHANNEL - Q₁, 2N7002 Section (@T_A = +25°C, unless otherwise specified.)

Character	istic	Symbol	Value	Unit
Drain-Source Voltage		V_{DSS}	60	V
Drain-Gate Voltage R _{GS} ≤ 1.0MΩ		V_{DGR}	60	V
Gate-Source Voltage	Continuous Pulsed	V_{GSS}	±20 ±40	V
Drain Current (Note 6)	Continuous Continuous @ +100°C Pulsed	I _D	115 73 800	mA

Maximum Ratings P-CHANNEL - Q₂, BSS84 Section (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage		V _{DSS}	-50	V
Drain-Gate Voltage $R_{GS} \le 20K\Omega$		V_{DGR}	-50	V
Gate-Source Voltage	Continuous	V_{GSS}	±20	V
Drain Current (Note 6)	Continuous	I _D	-130	mA

Note:

^{6.} Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Incorporated's suggested pad layout document, which can be found on our website at http://www.diodes.com/package-outlines.html.



Electrical Characteristics N-CHANNEL - Q₁, 2N7002 Section (@T_A = +25°C, unless otherwise specified.)

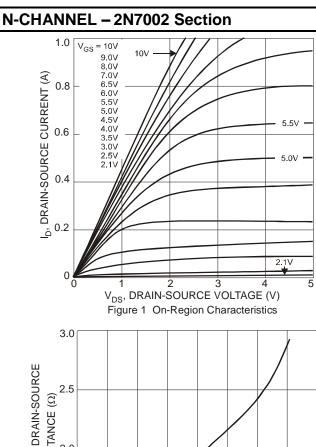
Characteristic		Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage		BV _{DSS}	60	70	_	V	$V_{GS} = 0V$, $I_D = 10\mu A$
Zero Gate Voltage Drain Current	@ T _C = +25°C @ T _C = +125°C	I _{DSS}	_	_	1.0 500	μΑ	$V_{DS} = 60V, V_{GS} = 0V$
Gate-Body Leakage		I _{GSS}	_	_	±10	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage		V _{GS(TH)}	1.0	_	2.5	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$
Static Drain-Source On-Resistance	@ T _J = +25°C	Ь		3.2	7.5	Ω	$V_{GS} = 5.0V, I_D = 0.05A$
	@ $T_J = +125$ °C	R _{DS(ON)}	_	4.4	13.5	12	$V_{GS} = 10V, I_D = 0.5A$
On-State Drain Current		I _{D(ON)}	0.5	1.0	_	Α	V _{GS} = 10V, V _{DS} = 7.5V
Forward Transconductance		g FS	80	_	_	mS	V _{DS} =10V, I _D = 0.2A
DYNAMIC CHARACTERISTICS							
Input Capacitance		C _{iss}	_	22	50	pF	
Output Capacitance		Coss	_	11	25	pF	$V_{DS} = 25V, V_{GS} = 0V, f = 1.0MHz$
Reverse Transfer Capacitance		C _{rss}	_	2.0	5.0	pF	
SWITCHING CHARACTERISTICS							
Turn-On Delay Time		t _{D(ON)}	_	7.0	20	ns	$V_{DD} = 30V, I_D = 0.2A,$
Turn-Off Delay Time	_	t _{D(OFF)}		11	20	ns	$R_L = 150\Omega$, $V_{GEN} = 10V$, $R_{GEN} = 25\Omega$

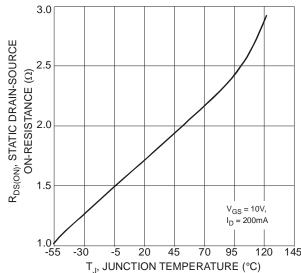
$\textbf{Electrical Characteristics P-CHANNEL-Q_2, BSS84 Section} \ (@T_A = +25^{\circ}C, \text{ unless otherwise specified.})$

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)	•						
Drain-Source Breakdown Voltage	BV _{DSS}	-50	_	_	V	$V_{GS} = 0V, I_{D} = -250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}			-1 -2 -100	μΑ μΑ nA	V _{DS} = -50V, V _{GS} = 0V, T _J = +25°C V _{DS} = -50V, V _{GS} = 0V, T _J = +125°C V _{DS} = -25V, V _{GS} = 0V, T _J = +25°C	
Gate-Body Leakage	I _{GSS}	_	_	±10	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(TH)}	-0.8	_	-2.0	V	$V_{DS} = V_{GS}$, $I_D = -1mA$	
Static Drain-Source On-Resistance	R _{DS(ON)}	_		10	Ω	$V_{GS} = -5V, I_D = -0.100A$	
Forward Transconductance	g _{FS}	0.05		_	S	$V_{DS} = -25V, I_{D} = -0.1A$	
DYNAMIC CHARACTERISTICS							
Input Capacitance	C _{iss}			45	pF		
Output Capacitance	Coss			25	pF	$V_{DS} = -25V, V_{GS} = 0V, f = 1.0MHz$	
Reverse Transfer Capacitance	C _{rss}	_	_	12	pF		
SWITCHING CHARACTERISTICS							
Turn-On Delay Time	t _{D(ON)}	_	10	_	ns	$V_{DD} = -30V, I_D = -0.27A,$	
Turn-Off Delay Time	t _{D(OFF)}	_	18	_	ns	$R_{GEN} = 50\Omega$, $V_{GS} = -10V$	

Note: 7. Short duration pulse test used to minimize self-heating effect.







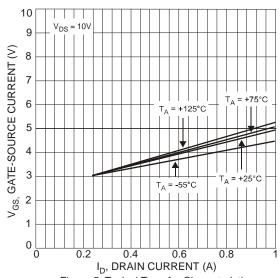
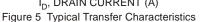


Figure 3 On-Resistance vs. Junction Temperature



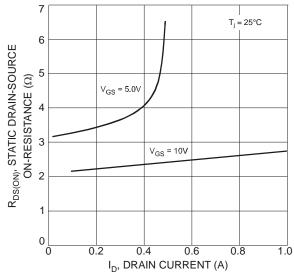
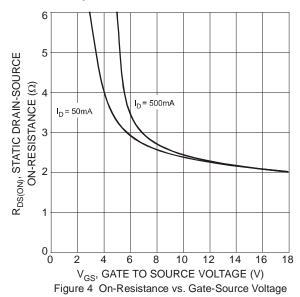


Figure 2 On-Resistance vs. Drain Current

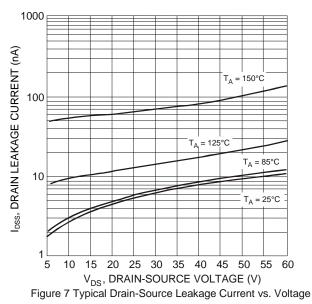


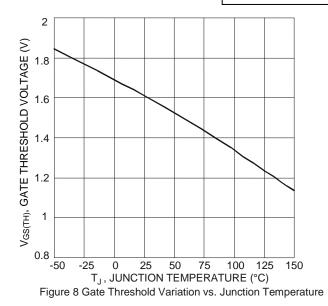
250 P_D, POWER DISSIPATION (mW) 200 150 100 50 0 75 100 125 150 175 50 T_A , AMBIENT TEMPERATURE (°C)

Figure 6 Max Power Dissipation vs. Ambient Temperature

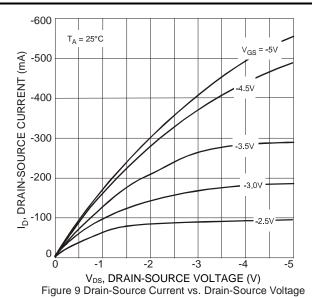


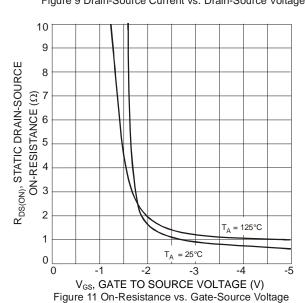


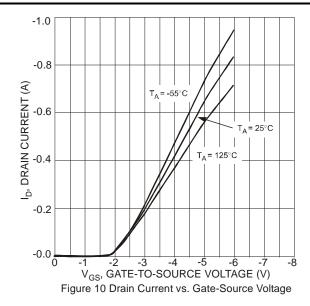




P-CHANNEL - BSS84 Section







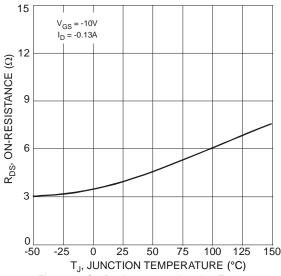


Figure 12 On-Resistance vs. Junction Temperature

March 2018

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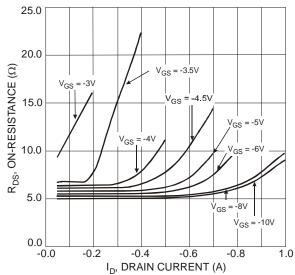


Figure 13 On-Resistance vs. Drain Current

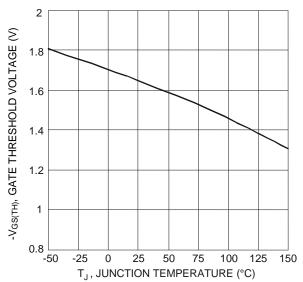


Figure 15 Gate Threshold Variation vs. Junction Temperature

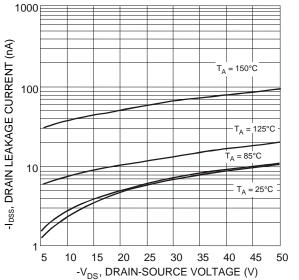


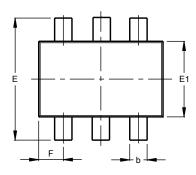
Figure 14 Typical Drain-Source Leakage Current vs. Voltage

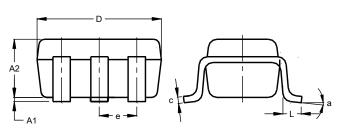


Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT363



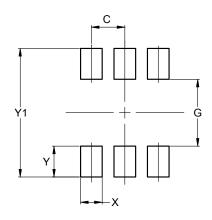


	SOT363							
Dim	Min Max Typ							
A1	0.00	0.10	0.05					
A2	0.90	1.00	0.95					
b	0.10	0.30	0.25					
C	0.10	0.22	0.11					
D	1.80	2.20	2.15					
Е	2.00	2.20	2.10					
E1	1.15	1.35	1.30					
е	C).650 E	SC					
F	0.40	0.45	0.425					
L	0.25	0.40	0.30					
а	0°	8°						
All I	Dimen	sions	in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT363



Dimensions	Value (in mm)
С	0.650
G	1.300
Х	0.420
Y	0.600
V1	2 500



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